

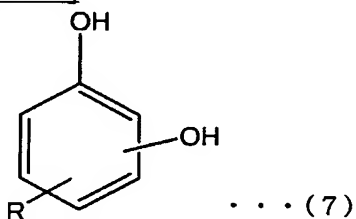
**AMENDMENTS TO THE CLAIMS, COMPLETE LISTING OF CLAIMS IN
ASCENDING ORDER WITH STATUS INDICATOR**

1. (Currently Amended) A positive-type photoresist comprising:

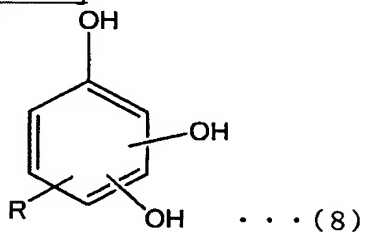
a novolac resin which has a benzene nucleus containing two or more hydroxyl groups and has a weight-average molecular weight of 1,000 to 20,000 and/or a derivative of the novolac resin,

said novolac resin being obtained by alternating copolymerization of at least one kind of monomers represented by the following formulas (7) to (16) and at least one kind of monomers represented by the following formulas (17) to (26), and wherein at least one kind of monomers represented by the following formulas (7), (8), (17), and (18) each containing two or more hydroxyl groups is used as the monomer for alternating copolymerization:

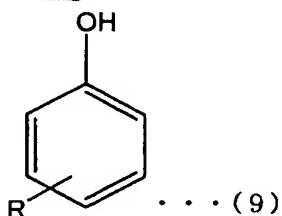
[Chem. 43]



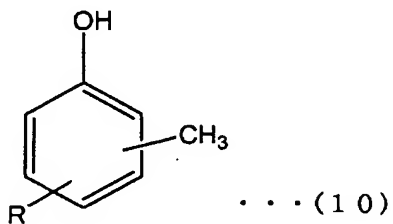
[Chem. 44]



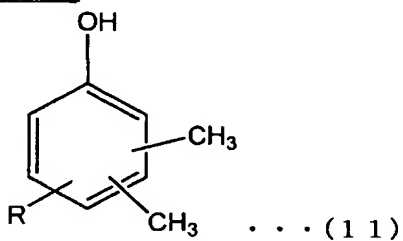
[Chem. 45]



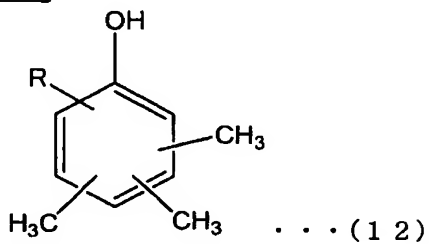
[Chem. 46]



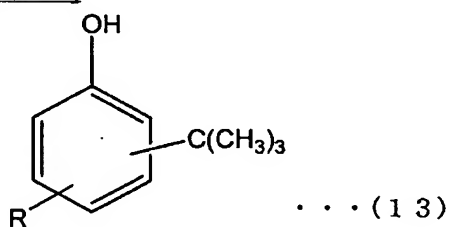
[Chem. 47]



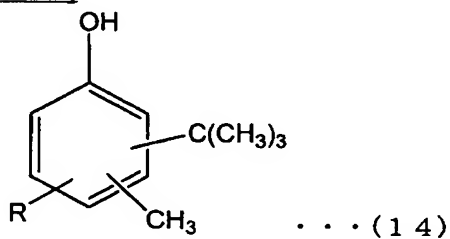
[Chem. 48]



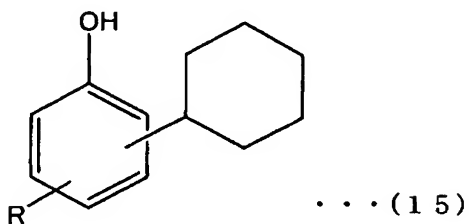
[Chem. 49]



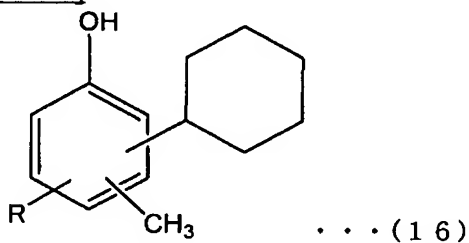
[Chem. 50]



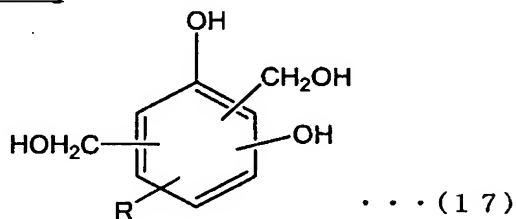
[Chem. 51]



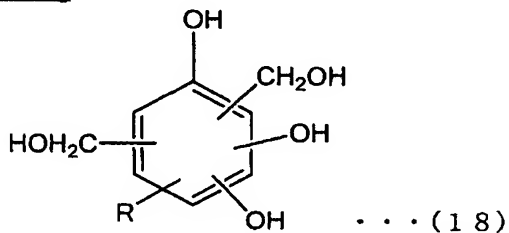
[Chem. 52]



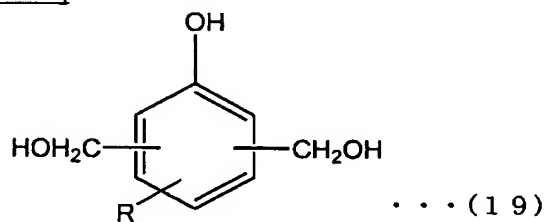
[Chem. 53]



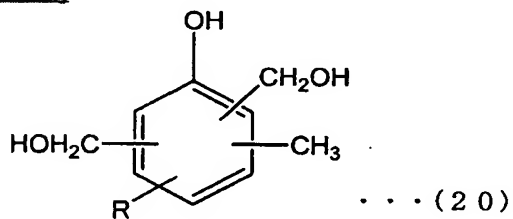
[Chem. 54]



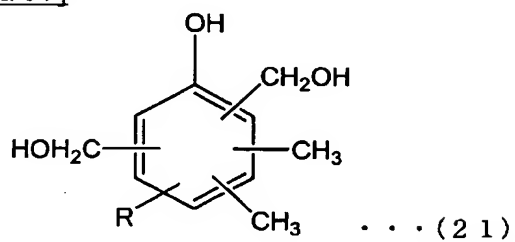
[Chem. 55]



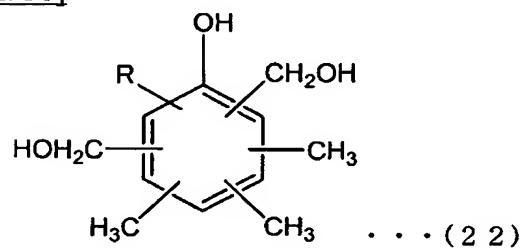
[Chem. 56]



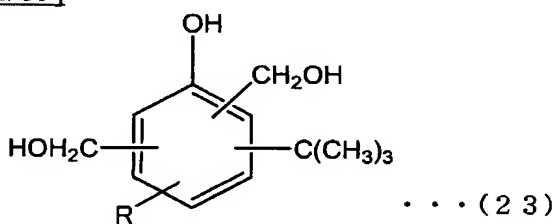
[Chem. 57]



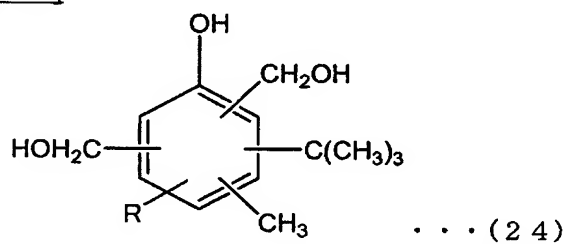
[Chem. 58]



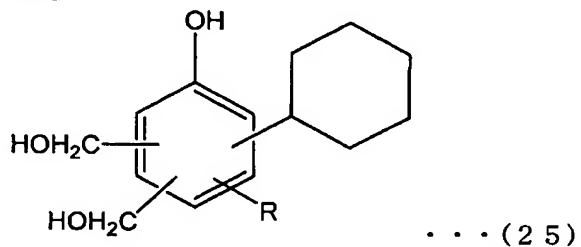
[Chem. 59]



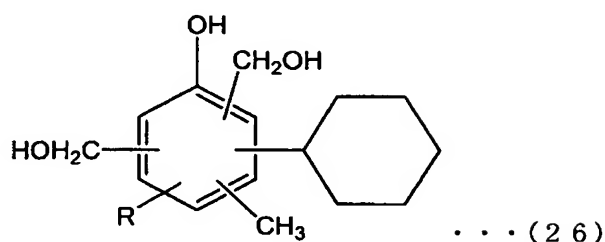
[Chem. 60]



[Chem. 61]



[Chem. 62]



where R in each of the formulas (7) to (26) represents a hydrogen atom or a lower alkyl group having 6 or less carbon atoms.

Claims 2-4 (Canceled).

5. (Currently Amended) The positive-type photoresist according to claim-41, wherein 30 parts by weight or more of the total amount of the monomers represented by the formulas (7), (8), (17), and (18) each containing two or more hydroxyl groups is used with respect to 100 parts by weight of total amount of the monomers represented by the formulas (7) to (16) and the monomers represented by the formulas (17) to (26).

6. (Currently Amended) The positive-type photoresist according to ~~any one of claims 1 to 5~~ claim 1 or 5, wherein the derivative of the novolac resin is obtained by replacing some of the hydroxyl groups of the novolac resin with a substituent.

7. (Original) The positive-type photoresist according to claim 6, wherein some of the hydroxyl groups are esterified and/or etherified.

8. (Currently Amended) The positive-type photoresist according to claim ~~6 or 7~~, wherein the replacement of some of the hydroxyl groups with a substituent is carried out using at least one compound selected from the group consisting of alkyl ethers, aryl ethers, benzyl ethers, triarylmethyl ethers, trialkylsilyl ethers, and tetrahydropyranyl ethers.

9. (Currently Amended) The positive-type photoresist according to claim ~~6 or 7~~, wherein the replacement of some of the hydroxyl groups with a substituent is carried out using at least

one compound selected from the group consisting of acetate, benzoate, methanesulfonic acid esters, and benzenesulfonic acid esters.

10. (Currently Amended) The positive-type photoresist according to ~~any one of~~ claims 1 to ~~9~~, further comprising a photosensitive compound.

11. (Original) The positive-type photoresist according to claim 10, wherein 5 to 50 parts by weight of the photosensitive compound is mixed with 100 parts by weight of total amount of the novolac resin and a derivative of the novolac resin.

12. (Currently Amended) The positive-type photoresist according to ~~any one of~~ claims 1 to ~~9~~, wherein the derivative of the novolac resin is a photosensitive novolac resin obtained by reacting the novolac resin with a photosensitive compound.

13. (Original) The positive-type photoresist according to claim 12, wherein the photosensitive novolac resin is one obtained by reacting 5 to 50 parts by weight of the photosensitive compound with 100 parts by weight of the novolac resin.

14. (Original) The positive-type photoresist according to claim 12 or 13 which comprises the novolac resin and the photosensitive novolac resin, wherein the photosensitive novolac resin is obtained by reacting 10 to 60 parts by weight of a photosensitive compound with 100 parts by weight of the novolac resin, and wherein the amount corresponding to the photosensitive compound is in the range of 5 to 50 parts by weight with respect to 100 parts by weight of total amount of the novolac resin and the photosensitive novolac resin.

15. (Currently Amended) The positive-type photoresist according to any one of claims 10 to ~~14~~ 13, wherein the photosensitive compound is 1,2-naphthoquinonediazidosulfonyl halide.

16. (Currently Amended) The positive-type photoresist according to ~~any one of~~ claims 1 or ~~5 to 15~~, further comprising an anionic surfactant in an amount of 1 to 20 parts by weight with

respect to 100 parts by weight of total amount of the novolac resin and a derivative of the novolac resin.

17. (Currently Amended) The positive-type photoresist according to ~~any one of~~ claims 1 or ~~5 to 16~~, further comprising colloidal silica in an amount of 50 to 300 parts by weight with respect to 100 parts by weight of total amount of the novolac resin and a derivative of the novolac resin.

18. (Currently Amended) The positive-type photoresist according to ~~any one of~~ claims 1 or ~~5 to 17~~, further comprising a viscosity-controlling agent in an amount of 100 to 700 parts by weight with respect to 100 parts by weight of total amount of the novolac resin and a derivative of the novolac resin.

19. (Currently Amended) A method for manufacturing a structure having a circuit formed using a resist pattern, comprising the steps of:

forming a resist film on a surface of a substrate by the use of the positive-type photoresist according to ~~any one of~~ claims 1 to 18;
exposing the resist film to light and carrying out development;
forming a circuit by the use of the resist pattern; and
removing the resist film.

20. (Original) The method for manufacturing a structure having a circuit formed using a resist pattern according to claim 19, wherein development is carried out using as a developer, an aqueous alkali solution whose alkali substance content is 0.3 wt% or less, in the step of exposing the resist film to light and carrying out development.

21. (Original) A method for manufacturing a structure having a circuit formed using the resist pattern according to claim 19 or 20, wherein a resist film is removed with ozone water in the step of removing the resist film.